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S86: (1) "9213802"
 S12: (1) "09213802"
 S13: (1) "11169199"
 S14: (7374) transistor and ((interlayer near2 (insulat\$)
 S15: (1396) S14 and (second adj gate)
 S16: (152) S15 and (second adj) (sidewall or (side adj w
 S17: (137) S16 and (conduct\$4)
 S18: (3) S17 and ((driv\$4 or control\$4) near2 transist
 S19: (3) Backward citation search 7
 S20: (20) Forward citation search 6
 S22: (161) S17 not (S18 S19 S20)
 S23: (161) S22 and (second adj (sidewall or (side adj w
 S24: (2) S23 and (compress\$4)
 S25: (6) S23 and (silicide and nitride and plug)
 S26: (38) S23 and (silicide and nitride and plug)
 S27: (164) ((driv\$4 or control\$4) near2 transistor) and
 S28: (95) S27 and ((side adj wall) or sidewall or space
 S29: (54) S28 not (S3 S4 S5 S24 S26 S18 S19 S20)
 S30: (53) S29 and (source and drain and substrate)

S17 and ((driv\$4 or control\$4) near2 transistor)
 S17 and ((driv\$4 or control\$4) near2 transistor)

| U | P | E | P | Document ID | Issue Date | Pages | Title | A | Current DB | Current |
|---|---|---|---|-----------------|------------|-------|--|---------|------------|---------|
| | M | F | M | US 20050051772 | 20050110 | 34 | Semiconductor device and method of manufacturing the same | 257/59 | 257/3 | |
| | M | F | M | US 20050041585 | 20050224 | 67 | Ferroelectric memory and method for manufacturing the same | 365/222 | 257/3 | |
| | M | F | M | US 20040232511 | 20041125 | 22 | Semiconductor device and method of manufacturing the same | 257/500 | | |
| | M | F | M | US 20040203267 | 20041014 | 31 | Semiconductor device and method of manufacturing the same | 438/258 | 257/3 | |
| | M | F | M | US 2004026740 | 20040812 | 32 | Semiconductor device and a method of manufacturing the same | 257/380 | 257/3 | |
| | C | F | C | US 20030227045 | 20031211 | 31 | Non-volatile semiconductor memory device | 257/315 | 257/3 | |
| | M | F | M | US 200302222294 | 20031204 | 37 | Nonvolatile semiconductor storage device | 257/398 | 257/3 | |
| | C | C | C | US 200302093372 | 20031030 | 41 | Nonvolatile semiconductor memory device and its manufacturing method | 438/257 | 257/3 | |
| | M | F | M | US 20030032422 | 20030610 | 28 | Semiconductor device and its manufacturing method | 438/193 | 257/3 | |
| | M | F | M | US 20020127791 | 20020912 | 43 | Semiconductor device and its manufacture method | 438/231 | 257/3 | |
| | M | F | M | US 20020045311 | 20020318 | 79 | Ferroelectric memory and method for manufacturing the same | 438/240 | 257/3 | |
| | | | | K1 | | | | | | |

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| Ref # | Hits | Search Query | DBs | Default Operator | Plurals | Time Stamp |
|-------|------|---|------------------------------------|------------------|---------|------------------|
| S1 | 1 | "20040178516" | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 12:36 |
| S2 | 18 | ogata-tamotsu.in. | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 12:37 |
| S3 | 1 | "20040178516" | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:47 |
| S4 | 18 | ogata-tamotsu.in. | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:47 |
| S5 | 7 | S4 and transistor and (hole or open\$4) and gate and substrate | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:50 |
| S6 | 1 | "9213802" | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:51 |
| S12 | 1 | "09213802" | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:53 |
| S13 | 1 | "11168199" | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 16:56 |
| S14 | 7374 | transistor and ((interlayer near2 (insulat\$4 or dielectric)) or (interdielectric or interinsulat\$4 or inter-dielectric or inter-insulat\$4 or (inter adj (dielectric or insulati\$4)))) and (open\$4 or hole) and source and drain and gate and (sidewall or (side adj wall) or spacer) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 17:00 |
| S15 | 1356 | S14 and (second adj gate) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 17:00 |
| S16 | 152 | S15 and (second adj (sidewall or (side adj wall) or spacer)) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 17:01 |
| S17 | 137 | S16 and (conduct\$4) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 17:02 |
| S18 | 36 | S17 and ((driv\$4 or control\$4) near2 transistor) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:14 |
| S19 | 3 | ("4305200" "4925807" "5061975").PN. | US-PGPUB; USPAT; USOCR | OR | ON | 2005/03/11 17:53 |
| S20 | 20 | ("5621232").URPN. | USPAT | OR | ON | 2005/03/11 17:56 |
| S22 | 101 | S17 not (S18 S19 S20) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:04 |

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|-----|-----|--|------------------------------------|----|----|------------------|
| S23 | 101 | S22 and (second adj (sidewall or (side adj wall) or spacer)) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:04 |
| S24 | 2 | S23 and (compress\$4) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:05 |
| S25 | 0 | S23 and (silicide and nitride and plug) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:07 |
| S26 | 38 | S23 and (silicide and nitride and plug) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:14 |
| S27 | 104 | ((drv\$4 or control\$4) near2 transistor) and (load adj transistor) and gate and ((interlayer near2 (insulat\$4 or dielectric)) or interdielectric or interinsulat\$4 or inter-dielectric or inter-insulat\$4 or (inter adj (dielectric or insulati\$4))) and plug | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:16 |
| S28 | 55 | S27 and ((side adj wall) or sidewall or spacer) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:17 |
| S29 | 54 | S28 not (S3 S4 S5 S24 S26 S18 S19 S20) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:17 |
| S30 | 53 | S29 and (source and drain and substrate) | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:18 |
| S31 | 40 | S30 and gate and nitride and oxide | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:25 |
| S32 | 13 | S30 not S31 | US-PGPUB; USPAT; EPO; JPO; IBM_TDB | OR | ON | 2005/03/11 18:25 |